

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09314 DT-01-09

Silicon Planar Type

Diode

# 1S2460~1S2462

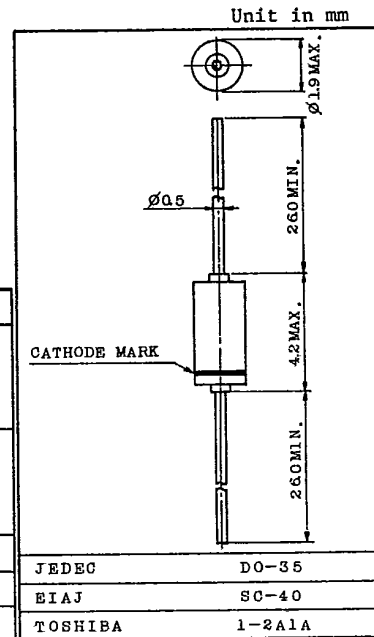
GENERAL PURPOSE RECTIFIER APPLICATIONS.

FEATURES:

- . High Reverse Voltage :  $V_R=200V(\text{Min.})$  (1S2462)
- . Low Forward Voltage :  $V_F=1.0V(\text{Max.})$
- . Hermetically Sealed Miniature Glass Package.

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	1S2460	70	V
	1S2461	120	
	1S2462	220	
Reverse Voltage	1S2460	50	V
	1S2461	100	
	1S2462	200	
Maximum (Peak) Forward Current	$I_{FM}$	300	mA
Average Forward Current	$I_O$	100	mA
Surge Current (1 sec)	$I_{FSM}$	800	mA
Power Dissipation	P	250	mW
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 ~ 175	$^\circ\text{C}$

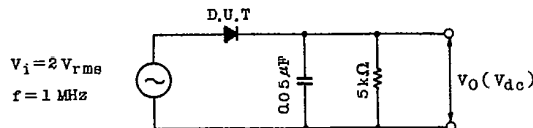


Weight : 0.14g

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F$	$I_F=100\text{mA}$	-	0.9	1.0	V
Reverse Current	1S2460	$V_R=50V$	-	-	1.2	$\mu\text{A}$
	1S2461	$V_R=100V$				
	1S2462	$V_R=200V$				
Rectification Efficiency	$\eta$	$f=1\text{MHz}, V_i=2V_{rms}$ (Fig.)	35	-	-	%
Total Capacitance	$C_T$	$V_R=0, f=1\text{MHz}$	-	5	10	pF

Fig. : TEST CIRCUIT



$$\eta = \frac{V_o (V_{dc})}{\sqrt{2} \times V_i (V_{rms})}$$

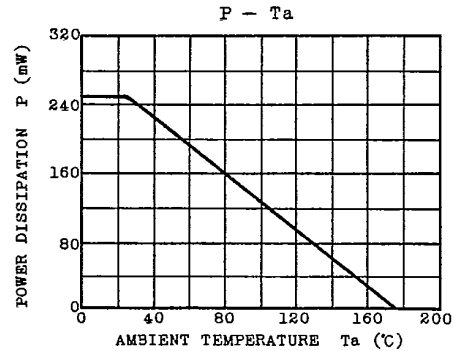
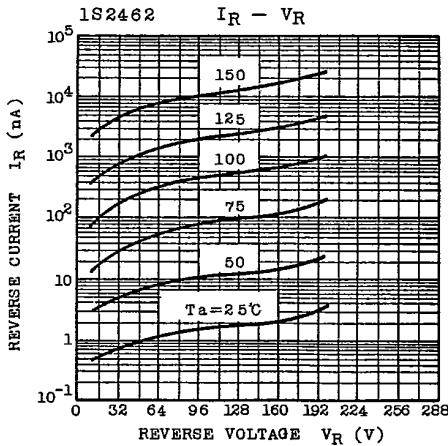
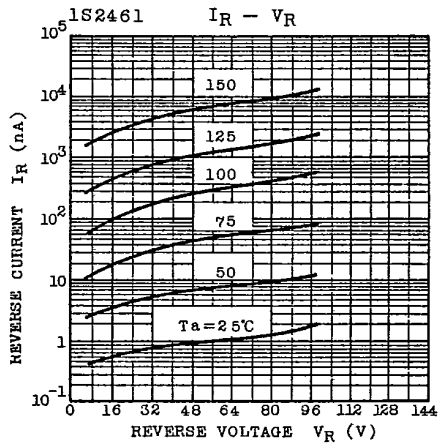
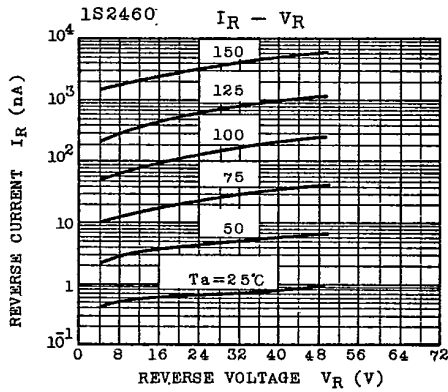
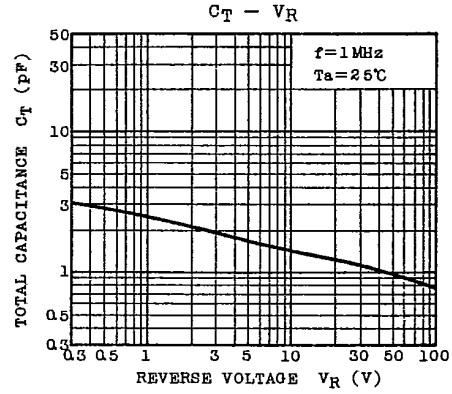
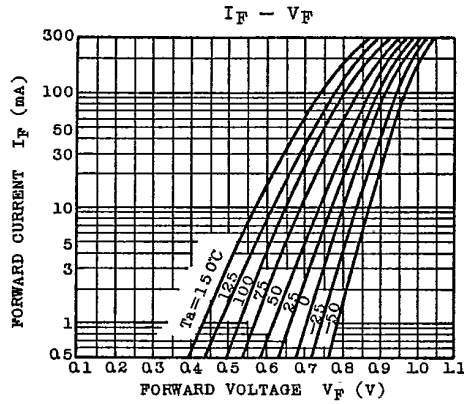
$$= 3.53 \times V_o (V_{dc}) (\%)$$

TOSHIBA CORPORATION

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